

The code for bulk PMOS is as mentioned below.

2D Coding:

```
#-----PMOS with triangular mesh -----#
```

```
GLOBAL  T=300 DopingScale=1e15 resistivemetal=false
```

```
#-----MESHING-----#
```

```
MESH    Type = S_Tri3
```

```
X.MESH  WIDTH=0.12      N.SPACES=8
```

```
X.MESH  WIDTH=0.035     N.SPACES=6
```

```
X.MESH  WIDTH=0.09      N.SPACES=15
```

```
X.MESH  WIDTH=0.035     N.SPACES=6
```

```
X.MESH  WIDTH=0.12      N.SPACES=8
```

```
Y.MESH  Y.TOP=-0.004  DEPTH=0.004  N.SPACES=4
```

```
Y.MESH          DEPTH=0.015  N.SPACES=4
```

```
Y.MESH          DEPTH=0.010  N.SPACES=4
```

```
Y.MESH          DEPTH=0.005  N.SPACES=8
```

```
Y.MESH          DEPTH=0.37   N.SPACES=10
```

```
#-----SPREAD-----#
```

```
#SPREAD  Location=Left Width=0.125 Upper=0 Lower=2 Thickness=0.02 Encroach=1
```

```
#SPREAD  Location=Right Width=0.125 Upper=0 Lower=2 Thickness=0.02 Encroach=1
```

```
#-----REGION-----#
```

```
REGION  Label=N.SUBSTRATE          Material=Si
```

```
REGION  Label=N.Oxide  IY.MAX=4          Material=Ox
```

```
REGION  Label=N.Source      X.MIN=0.0  X.MAX=0.155 IY.MAX=4  Material=Elec
```

REGION Label=N.Drain X.MIN=0.245 X.MAX=0.4 IY.MAX=4 Material=Elec

FACE Label=N.SUB Location=BOTTOM

FACE Label=N.GATE X.MIN=0.155 X.MAX=0.245 Location=Top

#-----DOPING-----#

DOPING Type=analytic

PROFILE Type=Uniform Ion=Donor N.PEAK=5E15 X.MIN=0.0 \

X.MAX=0.4 Y.TOP=0 Y.BOTTOM=0.4

PROFILE Type=analytic Ion=Donor N.PEAK=1E18 X.MIN=0.0 \

X.MAX=0.4 Y.TOP=0.00 Y.CHAR=0.02

PROFILE Type=analytic Ion=Acceptor N.PEAK=2E18 Y.Junction=0.005 \

X.MIN=0.0 X.MAX=0.15 XY.RATIO=1

PROFILE Type=analytic Ion= Acceptor N.PEAK=1E20 Y.Junction=0.02 \

X.MIN=0.0 X.MAX=0.120 XY.RATIO=0.5

PROFILE Type=analytic Ion= Acceptor N.PEAK=2E18 Y.Junction=0.005 \

X.MIN=0.25 X.MAX=0.4 XY.RATIO=1

PROFILE Type=analytic Ion= Acceptor N.PEAK=1E20 Y.Junction=0.02 \

X.MIN=0.280 X.MAX=0.4 XY.RATIO=0.5

Export VtkFile="PMOS2D.vtu" CgnsFile="PMOS2D.cgns"

